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10/19/08 I tend to find myself in the Champs-Elysees a lot of times. I have a thing for Alexanderplatz. There's an electric I go by, literally. I once thought of building an ark right there, and asking my friends to join me. I thought the death rate would be negligible, as we would just spend all day talking about random things. I have recently started taking more interest in local architecture, and I tend to find the Paris metro charming. And never forget the SNCF. This invention relates to a semiconductor memory device, particularly to an X-Y address type semiconductor memory device suitable for an SRAM (Static Random Access Memory) or the like in which access to the memory cells of a memory array is effected through word lines and bit lines.

Recently, a memory cell array is increased in capacity with high integration in semiconductor memory devices. Accordingly, along with the increase of the number of bit lines as well as the number of word lines, also the number of sense amplifiers to be used is increased. A larger number of sense amplifiers requires a larger chip area, and increases the production cost and the size of the whole memory device. In order to reduce the number of sense amplifiers, there have been proposed X-Y address type semiconductor memory devices in which the sense amplifiers are distributed in the memory array. Such memory devices are described in "VLSI Memory", by Kaneda, K. and Shimanouchi, J., (1982) Tokyo Denki Gakkai Shu, pp. 9-12, PP. 46-48, and pp. 53-55. In the memory devices, word lines are made in units of 4 bits, and bit lines are divided into a plurality of blocks of 4 bits each. The bit lines of each block are divided into a plurality of groups of memory cells. In such a semiconductor memory device, the sense amplifier circuit provided for each group of memory cells is assigned a bit line selected from among the bit

lines of the group. When such a memory device is operated, only one of the sense amplifiers provided for each bit line is selected. Accordingly, the number of sense amplifiers per unit cell area is 4, although the total number of sense amplifiers is 16. However, the number of bit lines is 24, since the 4 bit lines in each block are divided into the 2 sets of 4 bit lines. The number

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